

Important notice

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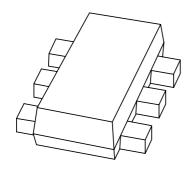
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2010EVLow V_F MEGA Schottky barrier diode

Product data sheet Supersedes data of 2002 Jun 24 2003 Aug 20



Low V_F MEGA Schottky barrier diode

PMEG2010EV

FEATURES

Forward current: 1 AReverse voltage: 20 V

Very low forward voltageUltra small SMD package

• Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

• Low voltage rectification

• High efficiency DC/DC conversion

• Switch mode power supply

• Inverse polarity protection

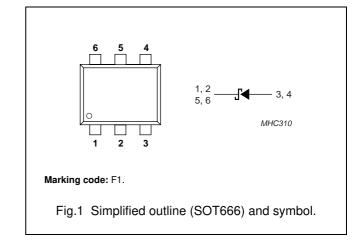
• Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection in a SOT666 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION	
1	cathode	
2	cathode	
3	anode	
4	anode	
5	cathode	
6	cathode	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		_	20	V
I _F	continuous forward current		_	1	Α
I _{FSM}	non-repetitive peak forward current	t = 8.3 ms half sinewave; JEDEC method; note 1	-	8	А
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

Note

1. Only valid if pins 3 and 4 are connected in parallel.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Mounted on printed circuit-board, 1 $\,\mathrm{cm^2}$ copper area.

Soldering

The only recommended soldering method is reflow soldering.

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	continuous forward voltage	I _F = 10 mA	240	270	mV
		I _F = 100 mA	300	350	mV
		I _F = 1000 mA; note 1; see Fig.2	480	550	mV
I _R	reverse current	V _R = 5 V; note 2	5	10	μΑ
		V _R = 8 V; note 2	7	20	μΑ
		V _R = 15 V; note 2; see Fig.3	10	50	μΑ
C _d	diode capacitance	V _R = 5 V; f = 1 MHz; see Fig.4	19	25	pF

Notes

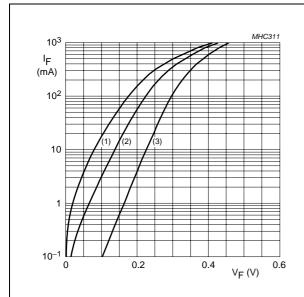
- 1. Only valid if pins 1, 2, 5 and 6 are soldered on a 1 cm^2 copper solder land.
- 2. Pulse test: t_p = 300 μ s; δ = 0.02.

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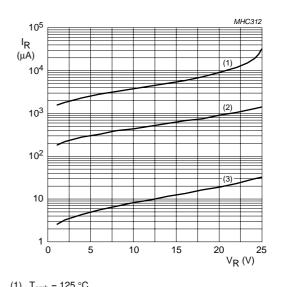
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GRAPHICAL DATA



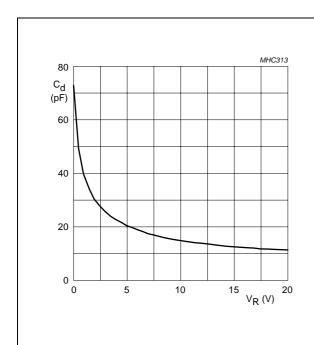
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; $T_{amb} = 25 \, ^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

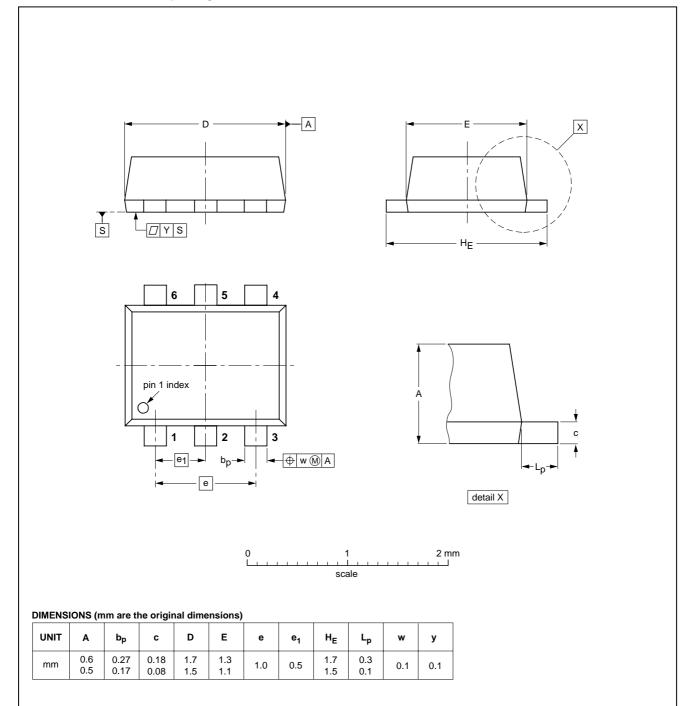
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



REFERENCES

EIAJ

JEDEC

EUROPEAN

PROJECTION

ISSUE DATE

01-01-04 01-08-27

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IEC

OUTLINE VERSION

SOT666

Low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

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Contact information

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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